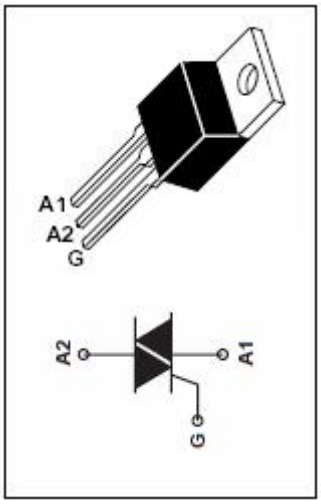
isc Triacs TIC236N

FEATURES

- With TO-220 package
- High current triacs
- Glass Passivated
- Max I_{GT} of 50 mA (Quadrants 1~3)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	800	V
V_{RRM}	Repetitive peak reverse voltage	800	V
$I_{T(RMS)}$	RMS on-state current (full sine wave)T_C=70℃	12	A
I_{TSM}	Non-repetitive peak on-state current	100	A
T_j	Operating junction temperature	110	℃
T_{stg}	Storage temperature	-40~125	℃
$R_{th(j-c)}$	Thermal resistance, junction to case	1.9	℃/W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	62.5	℃/W



ELECTRICAL CHARACTERISTICS (T_C=25℃ unless otherwise specified)

SYMBOL	PARAMETER		CONDITIONS	TYP.	MAX	UNIT
I_{DRM}	Repetitive peak off-state current		V_D=V_{DRM}, T_C=110℃		2.0	mA
I_{GT}	Gate trigger current	I	V_{supply} = 12 V†; R_L= 10Ω; $t_{p(g)}$ >20 μs	12	50	mA
		II		19	50	
		III		16	50	
		IV		34		
I_H	Holding current		V_{supply} = 12 V†,I_G= 0 initial I_{TM}=100mA		40	mA
V_{GT}	Gate trigger voltage**all quadrant**		V_{supply} = 12 V†; R_L= 10Ω; $t_{p(g)}$ >20 μs		2	V
V_{TM}	On-state voltage		I_T= 17A; I_G= 50mA		1.7	V